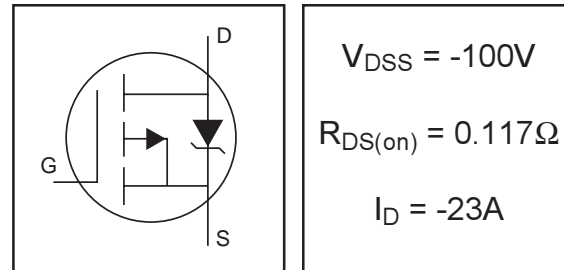


IRFP9140NPbF

HEXFET® Power MOSFET

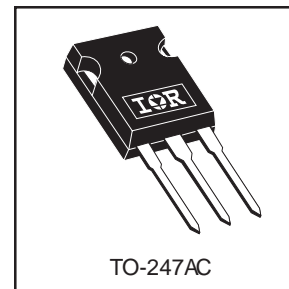
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- P-Channel
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-23	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-16	
I_{DM}	Pulsed Drain Current ①⑤	-76	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	140	W
	Linear Derating Factor	0.91	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑤	430	mJ
I_{AR}	Avalanche Current①	-11	A
E_{AR}	Repetitive Avalanche Energy①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	-5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

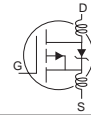
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient	---	40	

IRFP9140NPbF

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/°C	Reference to 25°C, I _D = -1mA ^⑤
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.117	Ω	V _{GS} = -10V, I _D = -13A ^④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	5.3	—	—	S	V _{DS} = -50V, I _D = 11A ^⑤
I _{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	V _{DS} = -100V, V _{GS} = 0V
		—	—	-250		V _{DS} = -80V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	97	nC	I _D = -11A
Q _{gs}	Gate-to-Source Charge	—	—	15		V _{DS} = -80V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	51		V _{GS} = -10V, See Fig. 6 and 13 ^{④⑤}
t _{d(on)}	Turn-On Delay Time	—	15	—	ns	V _{DD} = -50V I _D = -11A R _G = 5.1Ω R _D = 4.2Ω, See Fig. 10 ^{④⑤}
t _r	Rise Time	—	67	—		
t _{d(off)}	Turn-Off Delay Time	—	51	—		
t _f	Fall Time	—	51	—		
L _D	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	13	—		
C _{ISS}	Input Capacitance	—	1300	—	pF	V _{GS} = 0V V _{DS} = -25V f = 1.0MHz, See Fig. 5 ^⑤
C _{OSS}	Output Capacitance	—	400	—		
C _{RSS}	Reverse Transfer Capacitance	—	240	—		



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-23	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ^{①⑤}	—	—	-76		
V _{SD}	Diode Forward Voltage	—	—	-1.3	V	T _J = 25°C, I _S = -13A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	150	220	ns	T _J = 25°C, I _F = -11A
Q _{rr}	Reverse Recovery Charge	—	830	1200	μC	di/dt = -100A/μs ^④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 7.1mH
R_G = 25Ω, I_{AS} = -11A. (See Figure 12)

③ I_{SD} ≤ -11A, di/dt ≤ -470A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ Uses IRF9540N data and test conditions

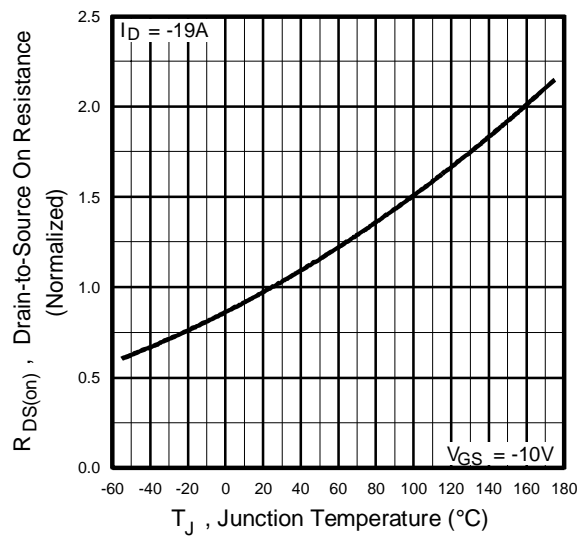
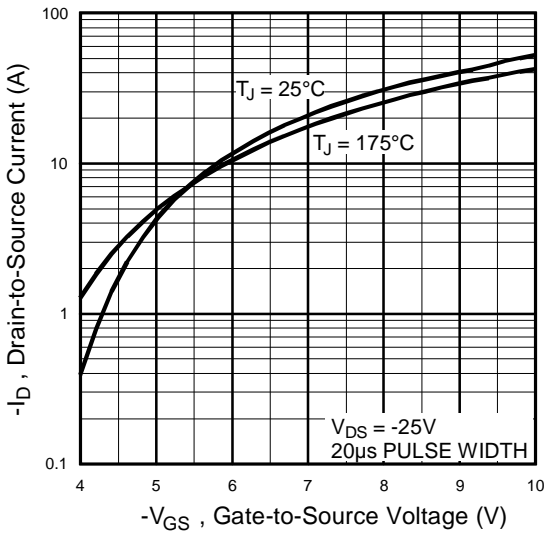
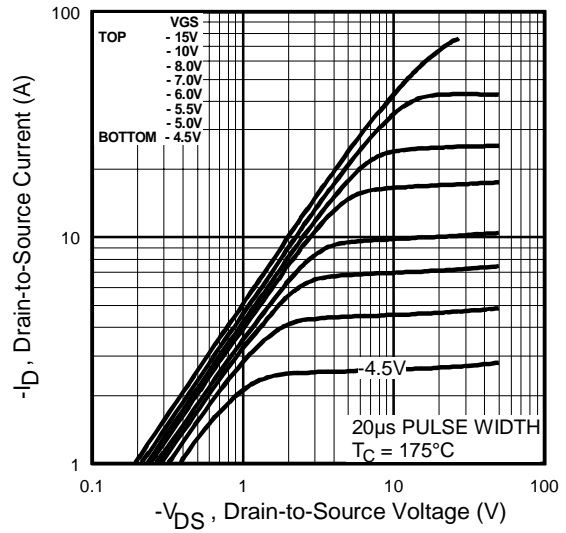
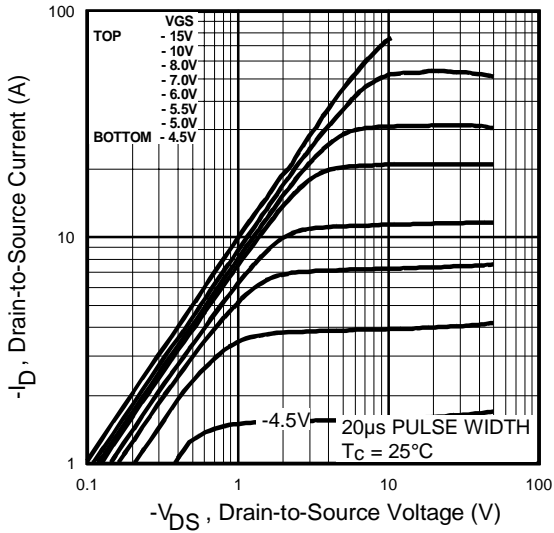


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

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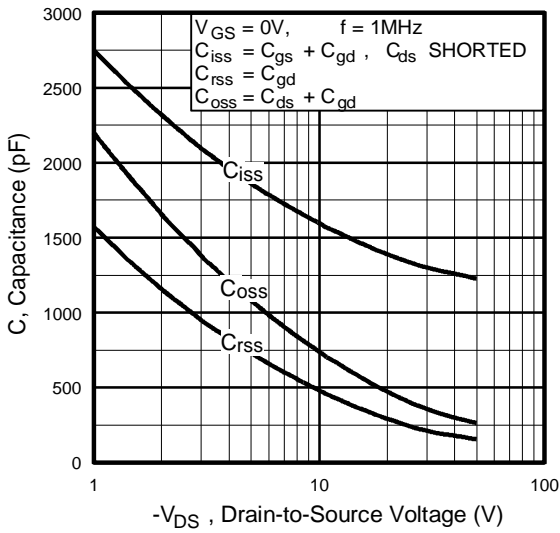


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

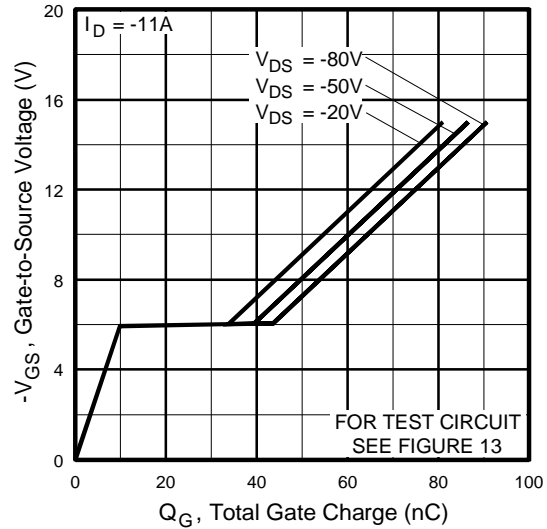


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

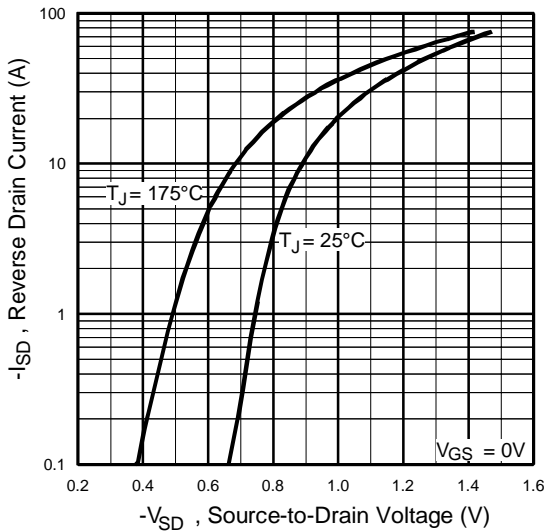


Fig 7. Typical Source-Drain Diode Forward Voltage

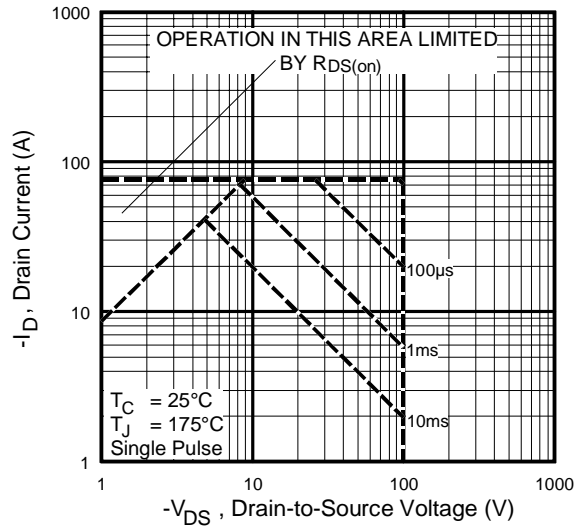


Fig 8. Maximum Safe Operating Area

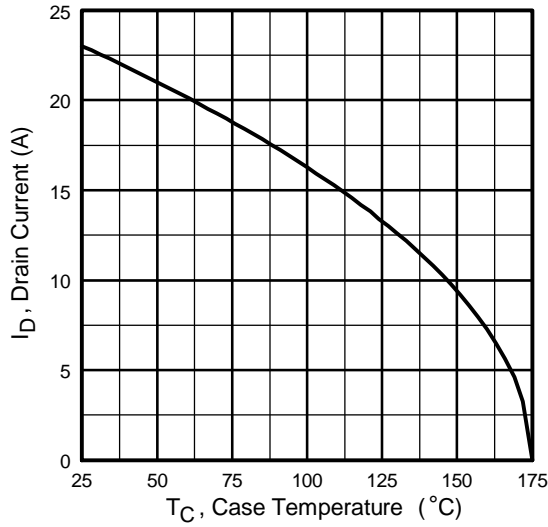


Fig 9. Maximum Drain Current Vs. Case Temperature

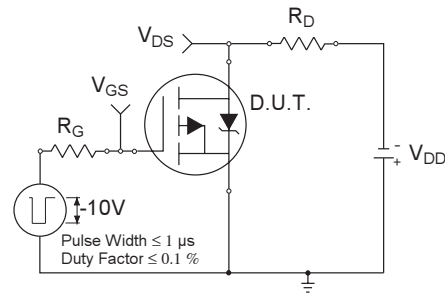


Fig 10a. Switching Time Test Circuit

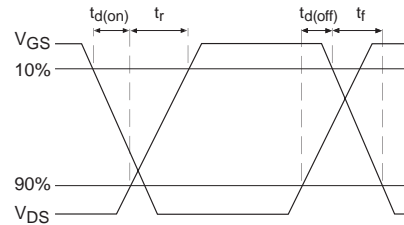


Fig 10b. Switching Time Waveforms

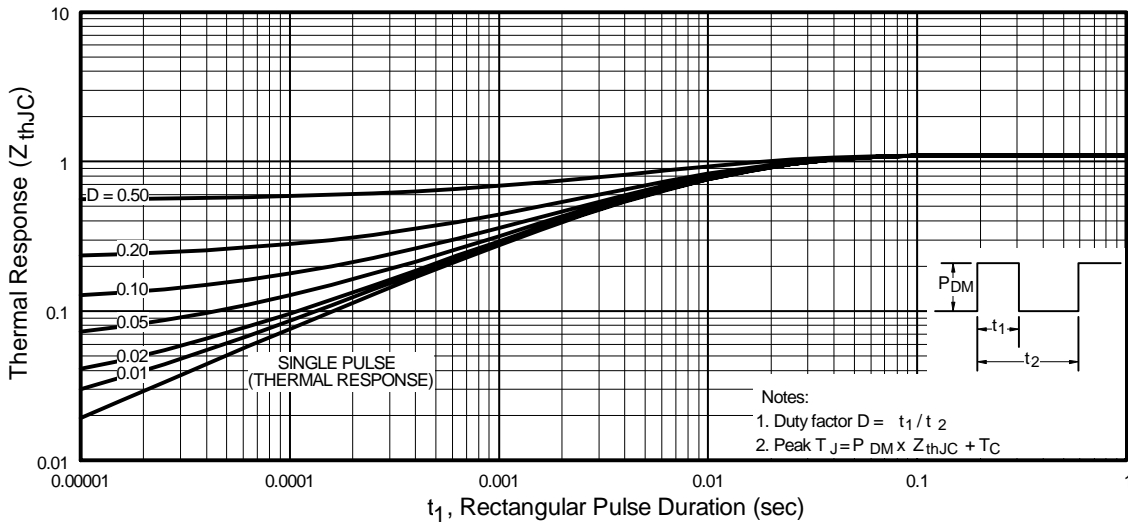


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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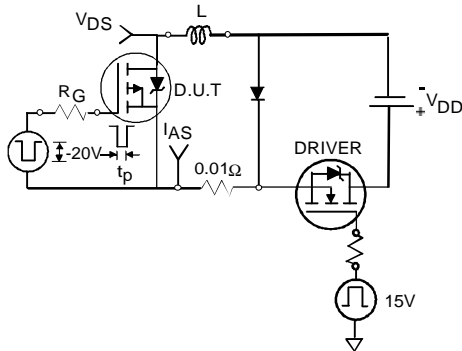


Fig 12a. Unclamped Inductive Test Circuit

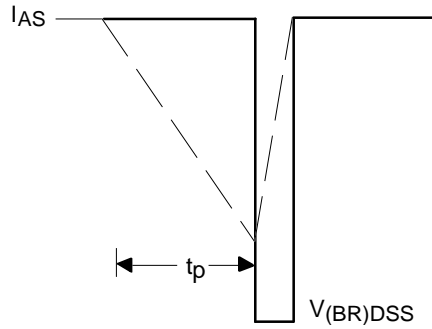


Fig 12b. Unclamped Inductive Waveforms

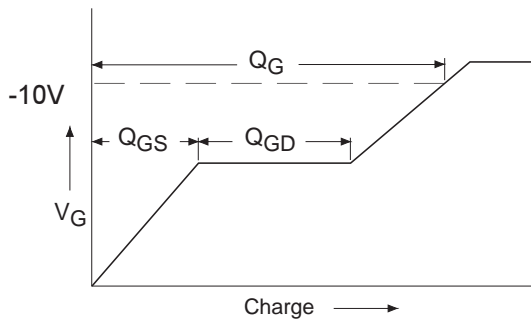


Fig 13a. Basic Gate Charge Waveform

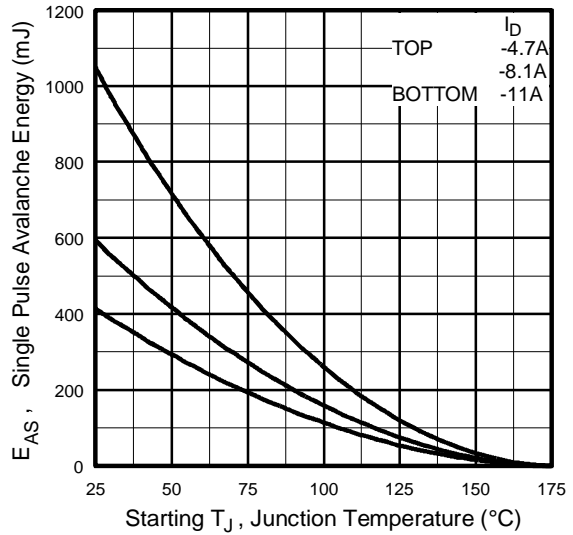


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

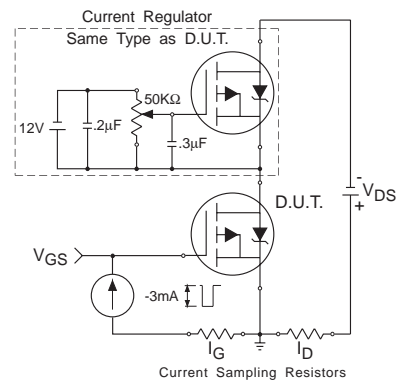
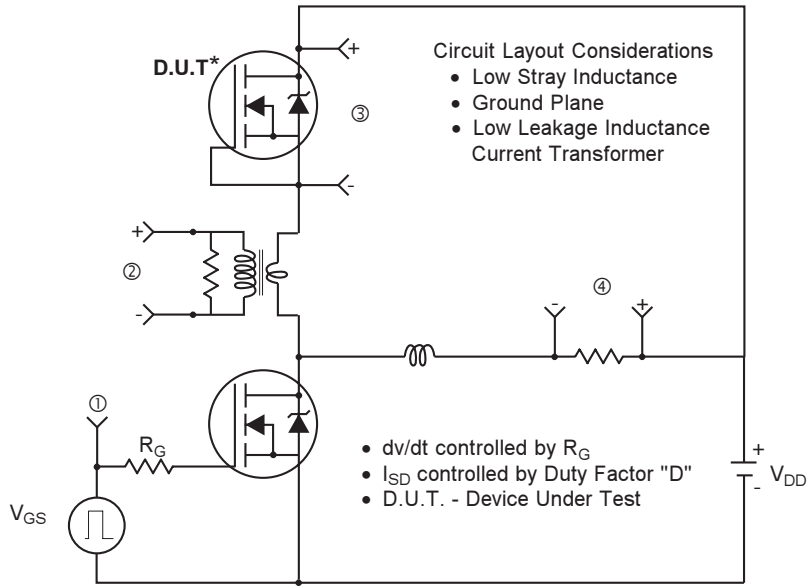
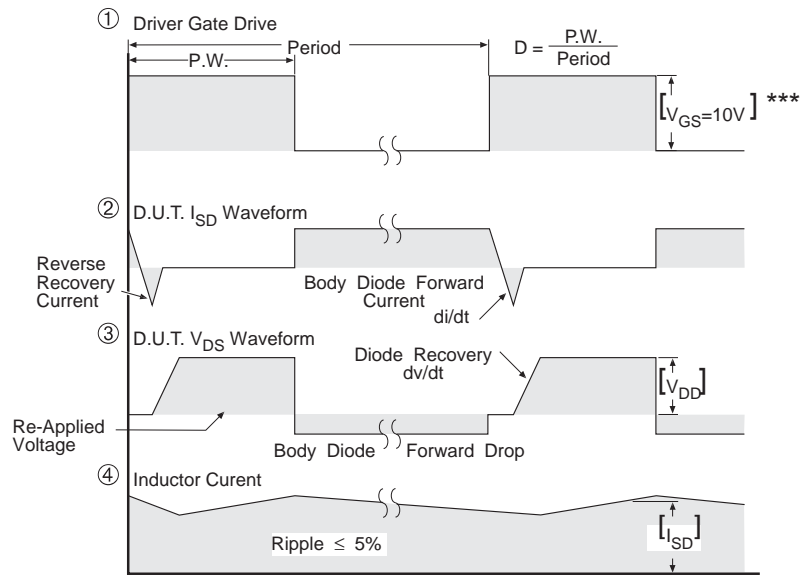


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



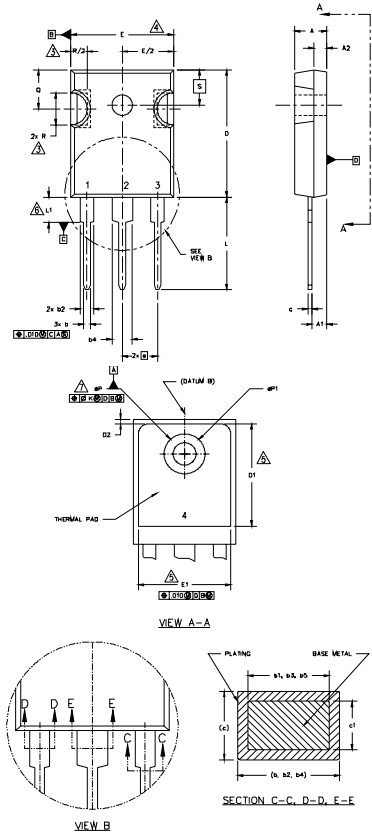
*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For P-Channel HEXFETS

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TO-247AC Package Outline Dimensions are shown in millimeters (inches)



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- CONTOUR OF SLOT OPTIONAL.
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
- LEAD FINISH UNCONTROLLED IN L1.
- ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].
- OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
c1	.015	.030	0.38	0.76	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.030	0.51	0.76	
E	.602	.625	15.29	15.87	4
E1	.540	-	13.72	-	
e	.215 BSC		5.46 BSC		
ØK	.010		2.54		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3		7.62 BSC		
ØP1	.140	.144	3.56	3.66	
Q	-	.275	-	6.98	
R	.209	.224	5.31	5.69	
S	.178	.216	4.52	5.49	
	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- GATE
- DRAIN
- SOURCE
- DRAIN

IGBTs, CoPACK

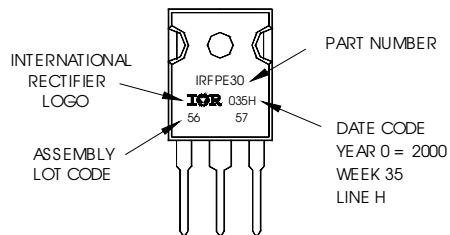
- GATE
- COLLECTOR
- EMITTER
- COLLECTOR

DIODES

- ANODE/OPEN
- CATHODE
- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"
Note: "P" in assembly line
position indicates "Lead-Free"



Data and specifications subject to change without notice.

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IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 07/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>